Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	1710	(257/774).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2004/07/07 09:18
S2	10	(("6054380") or ("6046104") or ("6069068") or ("6130161") or ("6184138") or ("6200899") or ("6189209") or ("5994211") or ("6150723") or ("6157081")).PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2004/07/07 10:21
S3	37	(("6204550") or ("6077779") or ("6096637") or ("6130156") or ("6140225") or ("6218279") or ("6225217") or ("6242789") or ("6225217") or ("6242789") or ("6271119") or ("6443743") or ("6569751") or ("5420070") or ("5318924") or ("5440070") or ("5306952") or ("5652182") or ("5514622") or ("5874355") or ("6143649") or ("6225698") or ("6225698") or ("6225698") or ("6093645") or ("6077338") or ("4330850") or ("6177338") or ("581581") or ("5975912") or ("6028360") or ("5975912") or ("6028360") or ("6093639") or ("6147000") or ("6093639") or ("6147000") or ("6146996") or ("6147000") or ("6146996") or ("6211084")) PN	US-PGPUB; USPAT; USOCR	OR	OFF	2004/07/07 10:21
S4	10	("20020024142" "20020036309" "5354712" "5472912" "5693564" "6028362" "6211085" "6258707" "6326301" "6436814").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2004/07/07 11:07
S5	66	hamamoto.in. and dram	US-PGPUB; USPAT; USOCR	OR	OFF	2004/07/07 11:07

Most Frequently Occurring Classifications of Patents Returned From A Search of 10/606,048 on July 07, 2004

Combined Classifications

23 257/E21.584 11 438/637 10 257/E21.577 10 257/E23.145 9 438/643 8 257/E21.585 8 438/627 8 438/672 7 438/624 7 438/648 6 257/774 6 438/622 6 438/629 6 438/687 5 257/E21.311 4 257/E21.578 4 257/E23.16 4 438/597 4 438/626 4 438/631 4 438/633 4 438/645 4 438/649 4 438/653 4 438/660 4 438/666 4 438/680 4 438/685 3 257/751 3 257/758 3 257/763 3 257/E21.033 3 257/E21.256 3 257/E21.257 3 257/E21.294 3 257/E21.314 3 257/E21.579 3 257/E21.582 3 257/E23.149

3 427/124

3 427/99 3 438/618 3 438/623 3 438/628 3 438/634 3 438/639 3 438/642 3 438/654 3 438/658 3 438/700 3 438/735 3 438/736 2 257/622 2 257/764 2 257/775 2 257/E21.313 2 257/E21.576 2 257/E21.583 2 257/E21.589 2 257/E21.591 2 438/131 2 438/132 2 438/257 2 438/28 2 438/467 2 438/529 2 438/601 2 438/625 2 438/630 2 438/638 2 438/644 2 438/655 2 438/656 2 438/663 2 438/675 2 438/678 2 438/681 2 438/682 2 438/688 2 438/720

11 438/637 (5 OR, 6 XR) Class 438: SEMICONDUCTOR DEVICE MANUFACTURING: PROCESS
438/584 COATING WITH ELECTRICALLY OR THERMALLY CONDUCTIVE MATERIAL
438/597 .To form ohmic contact to semiconductive material
438/618Contacting multiple semiconductive regions (i.e., interconnects)
438/622Multiple metal levels, separated by insulating layer (i.e., multiple level metallization)
438/637With formation of opening (i.e., viahole) in insulative layer
9 438/643 (1 OR, 8 XR) Class 438: SEMICONDUCTOR DEVICE MANUFACTURING: PROCESS
438/584 COATING WITH ELECTRICALLY OR THERMALLY CONDUCTIVE MATERIAL
438/597 .To form ohmic contact to semiconductive material
438/618Contacting multiple semiconductive regions (i.e., interconnects)
438/642Diverse conductors 438/643At least one layer forms a diffusion
barrier
8 438/627 (1 OR, 7 XR) Class 438: SEMICONDUCTOR DEVICE MANUFACTURING: PROCESS
438/584 COATING WITH ELECTRICALLY OR THERMALLY CONDUCTIVE MATERIAL
438/597 .To form ohmic contact to semiconductive material
438/618Contacting multiple semiconductive regions (i.e., interconnects)
438/622Multiple metal levels, separated by insulating layer (i.e., multiple level metallization)
438/625At least one metallization level formed of diverse conductive layers
438/627At least one layer forms a diffusion barrier
8 438/672 (0 OR, 8 XR) Class 438: SEMICONDUCTOR DEVICE MANUFACTURING: PROCESS
438/584 COATING WITH ELECTRICALLY OR THERMALLY CONDUCTIVE MATERIAL
438/597 .To form ohmic contact to semiconductive material
438/669And patterning of conductive layer 438/672Plug formation (i.e., in viahole)
7 438/624 (2 OR, 5 XR) Class 438: SEMICONDUCTOR DEVICE MANUFACTURING: PROCESS

	438/584	COATING WITH ELECTRICALLY OR THERMALLY CONDUCTIVE MATERIAL
	438/597	.To form ohmic contact to semiconductive material
	438/618	Contacting multiple semiconductive regions (i.e., interconnects)
	438/622	Multiple metal levels, separated by insulating layer (i.e., multiple level metallization)
	438/624	Separating insulating layer is laminate or composite of plural insulating materials
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1	438/648 Class 43	(1 OR, 6 XR) 38: SEMICONDUCTOR DEVICE MANUFACTURING: PROCESS
	438/584	COATING WITH ELECTRICALLY OR THERMALLY CONDUCTIVE MATERIAL
	438/597	.To form ohmic contact to semiconductive
	438/618	materialContacting multiple semiconductive regions (i.e., interconnects)
	438/642	Diverse conductors
	438/648	Having refractory group metal (i.e., titanium (Ti), zirconium (Zr), hafnium (Hf), vanadium (V),
		niobium (Nb), tantalum (Ta), chromium (Cr), molybdenum
		(Mo), tungsten (W), or alloy thereof)
6	257/774	(2 OR, 4 XR)
	Class 25 257/734	57: ACTIVE SOLID-STATE DEVICES COMBINED WITH ELECTRICAL CONTACT OR LEAD
	257/773	
	257/774	
6	438/622	(1 OR, 5 XR)
		88: SEMICONDUCTOR DEVICE MANUFACTURING: PROCESS
	438/584	COATING WITH ELECTRICALLY OR THERMALLY CONDUCTIVE MATERIAL
	438/597	.To form ohmic contact to semiconductive
	438/618	materialContacting multiple semiconductive regions
	400/010	(i.e., interconnects)
	438/622	Multiple metal levels, separated by insulating layer (i.e., multiple level metallization)
		insulating layer (i.e., multiple level metallization)
6	438/629	(2 OR, 4 XR) 38: SEMICONDUCTOR DEVICE MANUFACTURING: PROCESS
	Class 4	56. SEMICONDUCTOR DEVICE MANUFACTURING. PROCESS
	438/584	COATING WITH ELECTRICALLY OR THERMALLY CONDUCTIVE MATERIAL
	438/597	.To form ohmic contact to semiconductive material
	438/618	Contacting multiple semiconductive regions (i.e., interconnects)
	438/622	Multiple metal levels, separated by
	438/625	insulating layer (i.e., multiple level metallization)At least one metallization level formed of
		·

diverse conductive layers

438/629

.....Diverse conductive layers limited to viahole/plug

6 438/687

(4 OR, 2 XR)

Class 438: SEMICONDUCTOR DEVICE MANUFACTURING: PROCESS

438/584

COATING WITH ELECTRICALLY OR THERMALLY

CONDUCTIVE MATERIAL

438/597

.To form ohmic contact to semiconductive

material

438/687

.. Copper of copper alloy conductor

PLUS Search Results for S/N 10/606,048, Searched July 07, 2004 (Top 50)

The Patent Linguistics Utility System (PLUS) is a USPTO automated search system for U.S. Patents from 1971 to the present. PLUS is a query-by-example search system which produces a list of patents that are most closely related linguistically to the application searched. This search was prepared by the staff of the Scientific and Technical Information Center, SIRA.

6054380	6204550	6271119	6143649	5429989
6046104	6077779	6443743	6225698	5849367
6069068	6096637	6569751	6225698	5851581
6130161	6130156	5420070	5591672	5975912
6184138	6140225	5318924	5915202	6028360
6200899	6218279	6146991	6025269	6066557
6189209	6225217	5306952	6093645	6093639
5994211	6218279	5652182	6177338	6147000
6150723	6225217	5514622	4330850	6146996
6157081	6242789	5874355	5001079	6211084